

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	1.0Ω @ V <sub>GS</sub> = -4.5V	-0.58A
	1.5Ω @ V <sub>GS</sub> = -2.5V	-0.48A
	2.0Ω @ V <sub>GS</sub> = -1.8V	-0.41A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

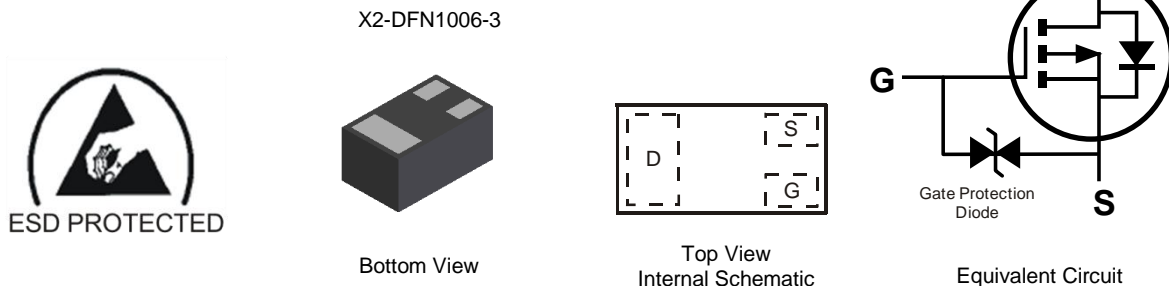
- Portable Electronics

## Features and Benefits

- Footprint of just 0.6mm<sup>2</sup> – 13 Times Smaller Than SOT23
- 0.4mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)

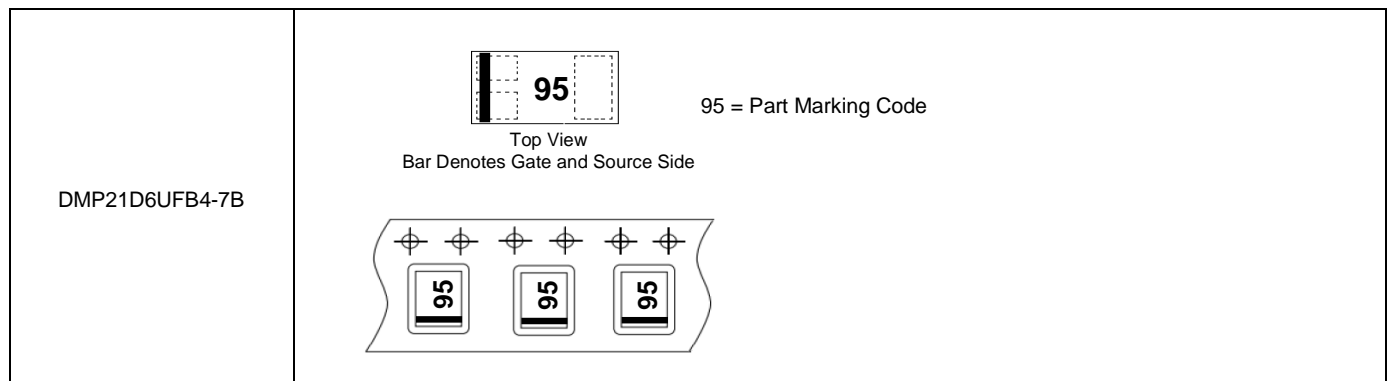


## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Quantity per Reel
DMP21D6UFB4-7B	95	7	8	2	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C (Note 5)	I <sub>D</sub>	-0.58	A
		T <sub>A</sub> = +70°C (Note 5)		-0.47	
		T <sub>A</sub> = +25°C (Note 6)		-0.81	
Maximum Body Diode Forward Current (Note 6)			I <sub>S</sub>	-0.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-5.0	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.51	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	240	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	0.98	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	128	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.67	1.0	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -100mA
			0.85	1.5		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -80mA
			1.0	2.0		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -40mA
Diode Forward Voltage	V <sub>SD</sub>	—	-1.0	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -300mA
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	46.1	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	7.2	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4.9	—	pF	
Gate Resistance	R <sub>G</sub>	—	350	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>G</sub>	—	0.5	—	nC	V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Total Gate Charge (V <sub>GS</sub> = -8V)	Q <sub>G</sub>	—	0.8	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	0.1	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	0.1	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	8.5	—	ns	V <sub>DD</sub> = -3V, V <sub>GS</sub> = -2.5V, R <sub>L</sub> = 300Ω, R <sub>G</sub> = 25Ω, I <sub>D</sub> = -100mA
Turn-On Rise Time	t <sub>R</sub>	—	4.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	20.2	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	19.2	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

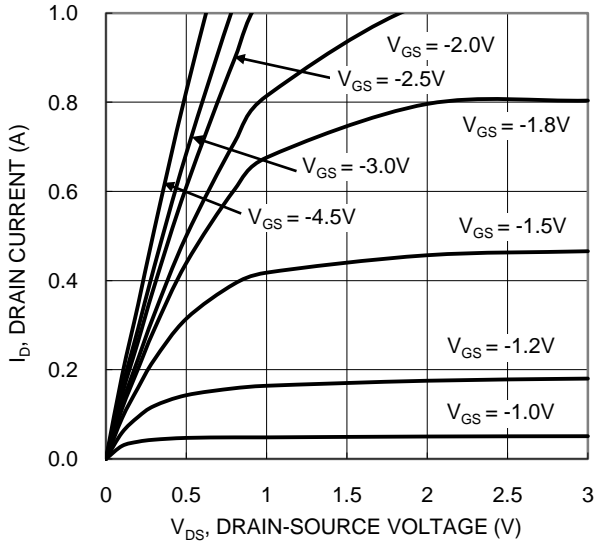


Figure 1. Typical Output Characteristic

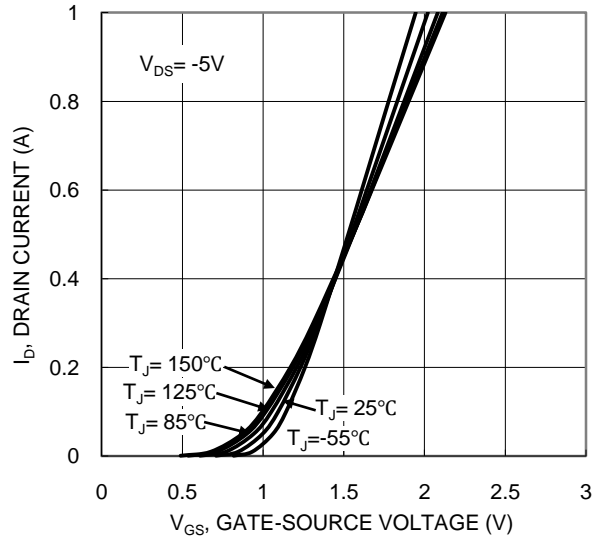


Figure 2. Typical Transfer Characteristic

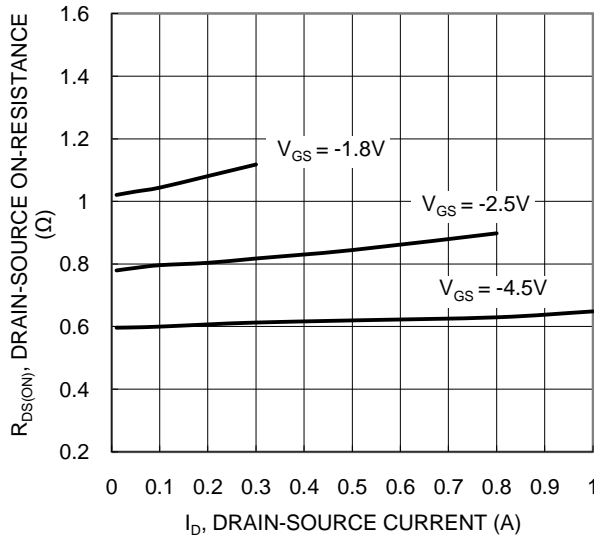


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

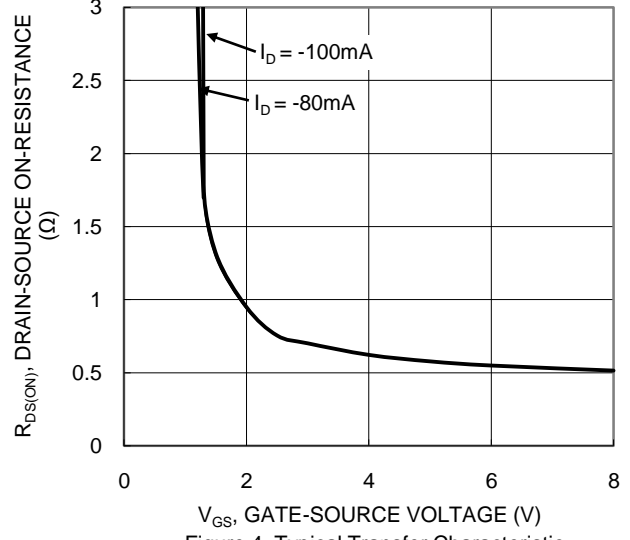


Figure 4. Typical Transfer Characteristic

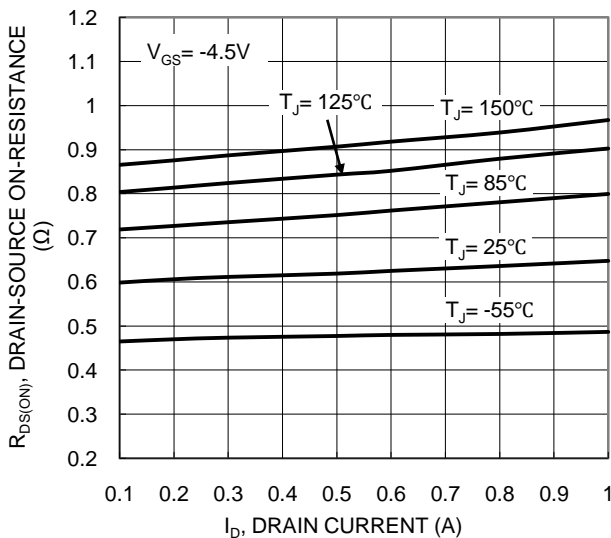


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

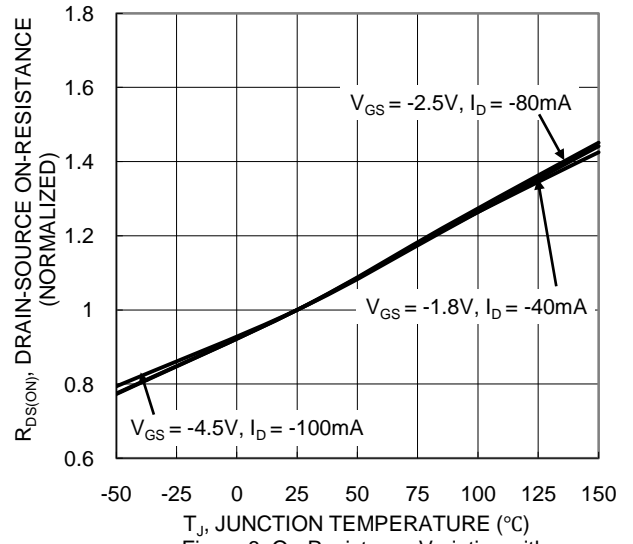


Figure 6. On-Resistance Variation with Temperature

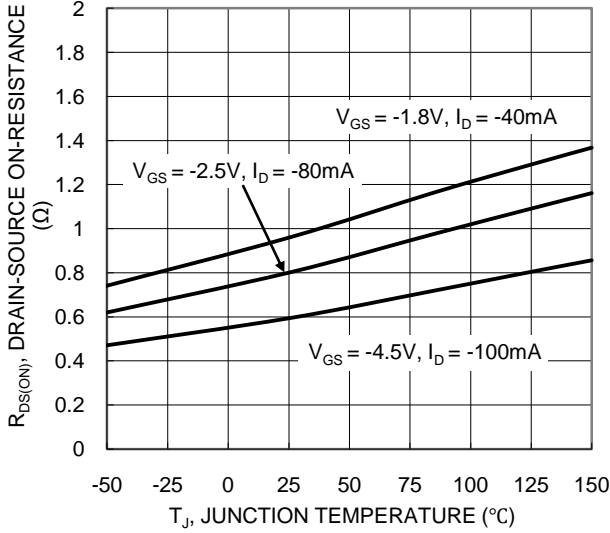


Figure 7. On-Resistance Variation with Temperature

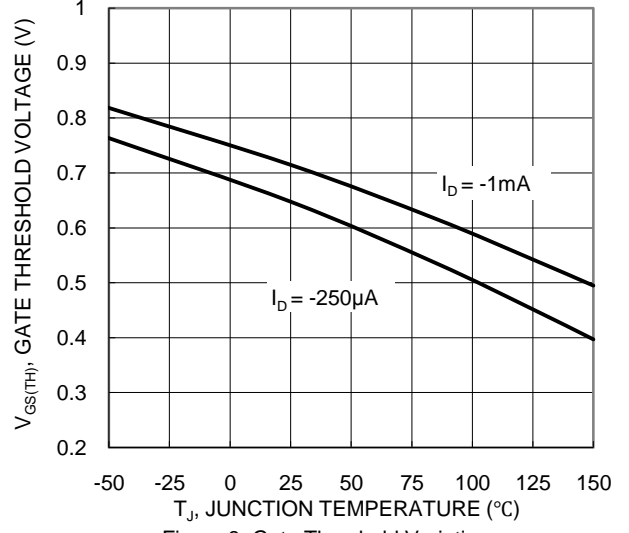


Figure 8. Gate Threshold Variation vs. Junction Temperature

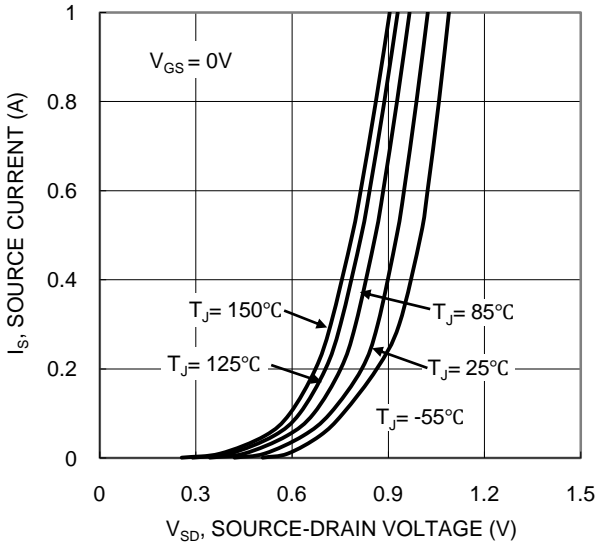


Figure 9. Diode Forward Voltage vs. Current

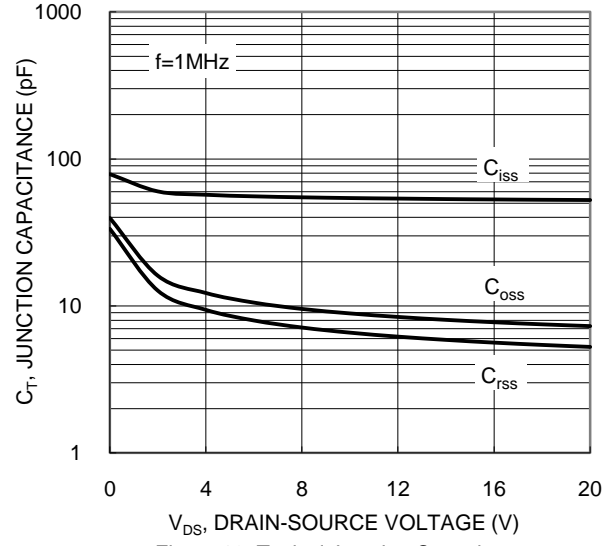


Figure 10. Typical Junction Capacitance

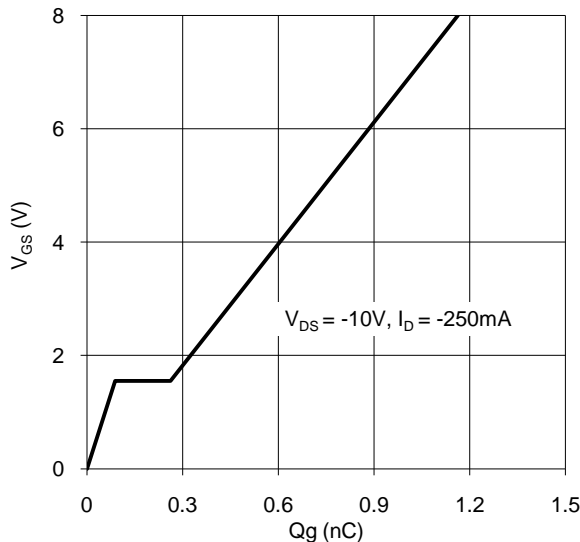


Figure 11. Gate Charge

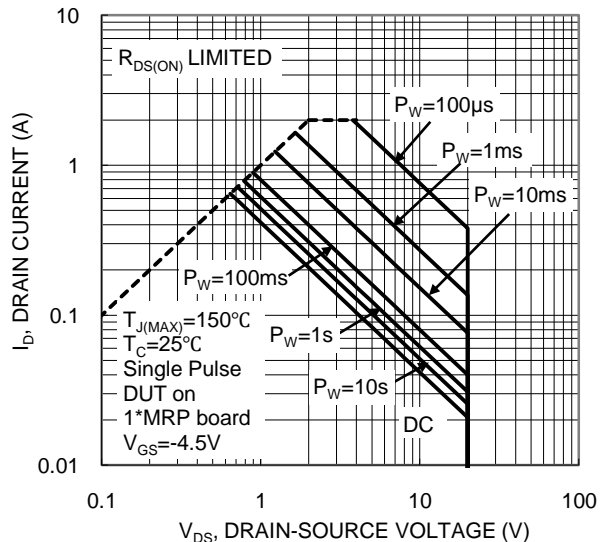


Figure 12. SOA, Safe Operation Area

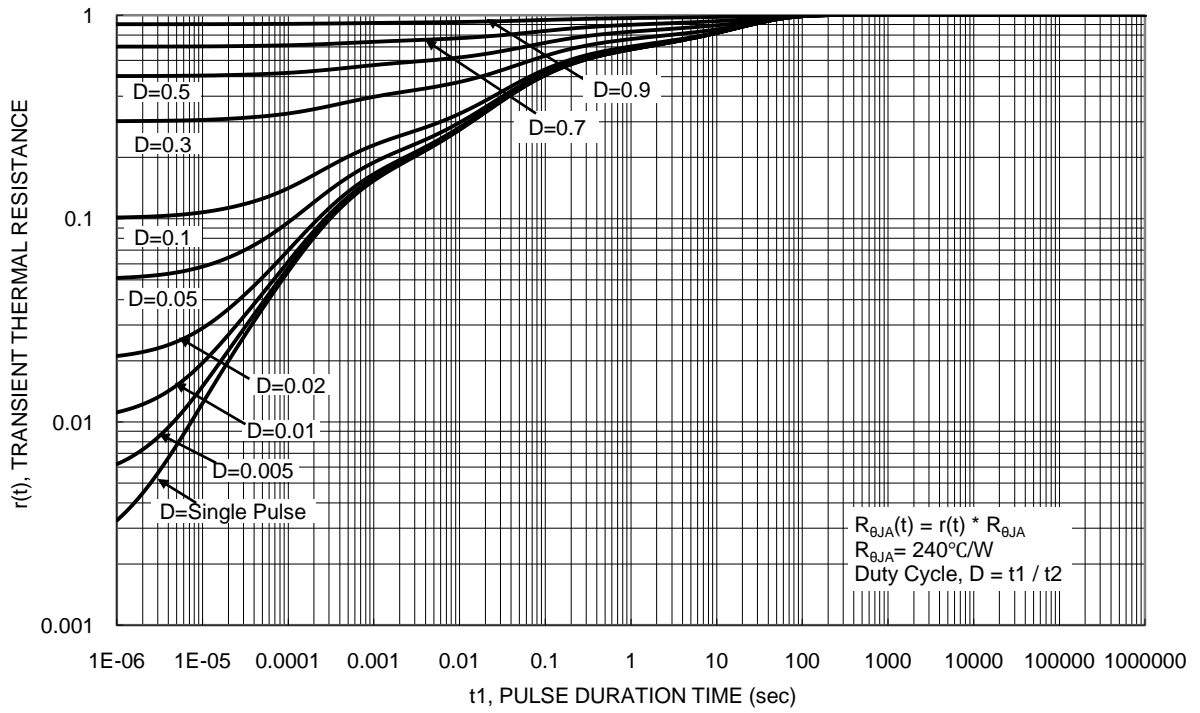
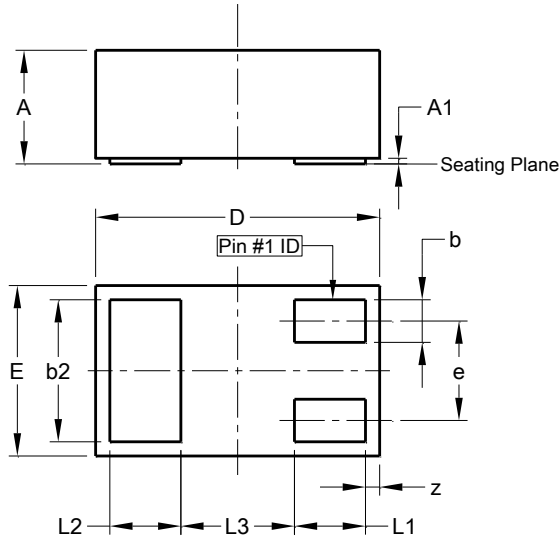


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1006-3**

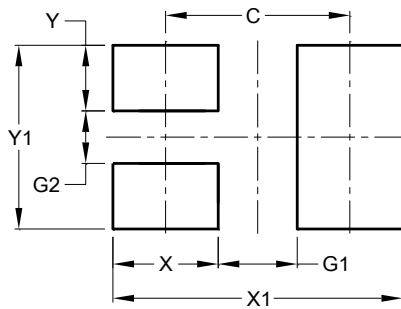


X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1006-3**



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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